NSN 5962-00-435-8313

Memory Microcircuit - Page 1 of 2

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Body Length:

Between 0.240 inches and 0.270 inches

Body Width:

Between 0.165 inches and 0.195 inches

Body Height:

Between 0.040 inches and 0.055 inches

Maximum Power Dissipation Rating:

30.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+200.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and expandable and negative outputs and positive outputs

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

Triple 3 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

20.00 nanoseconds propagation delay time, low to high level output and 20.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Special Features:

Formed leads

Test Data Document:

37695-618786 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

14 flat leads

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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